

2N4123



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage 30		V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4123	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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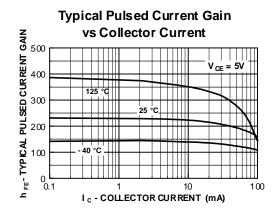
NPN General Purpose Amplifier (continued)

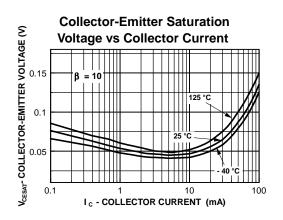
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_{E} = 0$		50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		50	nA
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 2.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$	50 25	150	
ON CHAR	ACTERISTICS*				
	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{R} = 5.0 \text{ mA}$	25	0.3	V
V _{CE(sat)} V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V
BE(out)	, , , , , , , , , , , , , , , , , , ,	, <u>-</u>			
SMALL S	IGNAL CHARACTERISTICS				
C _{ob}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 100 \text{ kHz}$		4.0	pF
C _{ib}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, f = 0.1 \text{ MHz}$		8.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz $I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$	50	200	
		f = 100 MHz	2.5		
f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}$ f = 100 MHz	250		MHz
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ R_{S} = 1.0 k\Omega, \\ B_{W} = 10 \text{ Hz to } 15.7 \text{ kHz}$		6.0	dB

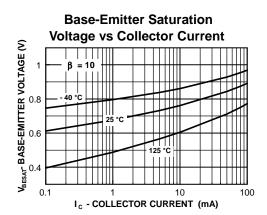
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

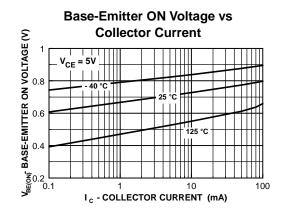
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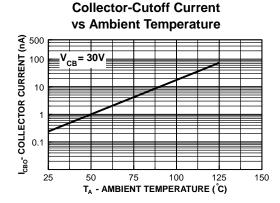
Typical Characteristics

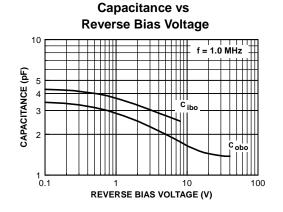






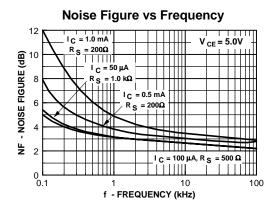


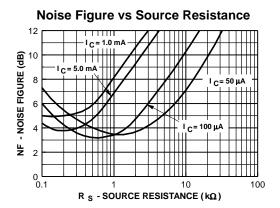


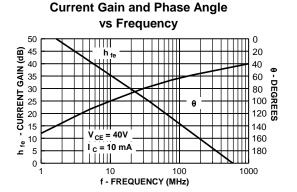


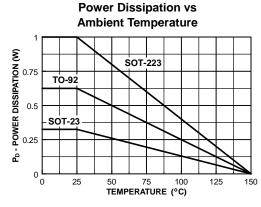
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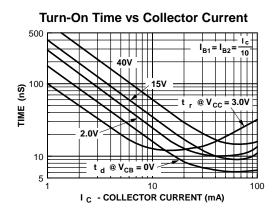
Typical Characteristics (continued)

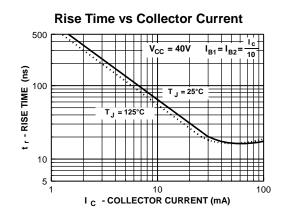








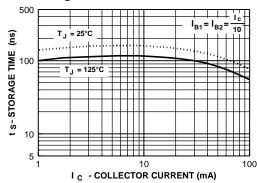




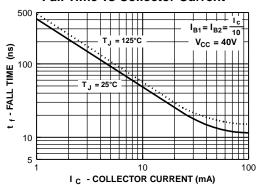
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Typical Characteristics (continued)

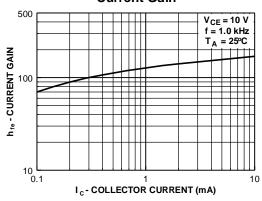




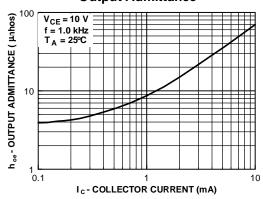
Fall Time vs Collector Current



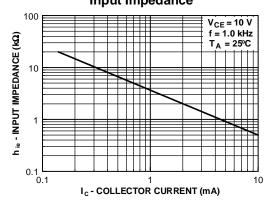
Current Gain



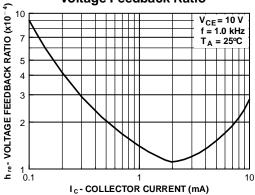
Output Admittance



Input Impedance



Voltage Feedback Ratio



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Test Circuits

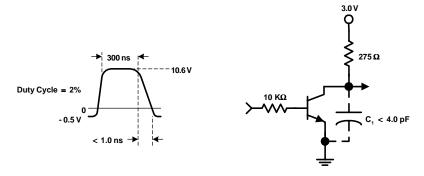


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

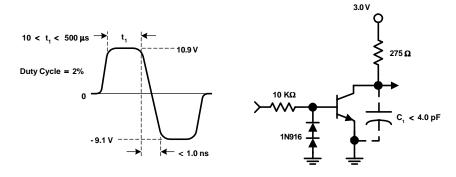


FIGURE 2: Storage and Fall Time Equivalent Test Circuit

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